

In the Claims:

Claim 1 (currently amended): An integrated circuit chip comprising:

 a first interconnect metal layer;

 a first intermetallic dielectric layer situated over said first interconnect metal layer;

 a metal resistor situated over said first intermetallic dielectric layer and below a second intermetallic dielectric layer;

 a second interconnect metal layer over said second intermetallic dielectric layer;

 a first intermediate via connected to a first terminal of said metal resistor, said first intermediate via being further connected to a first metal segment patterned in said second interconnect metal layer;

 a second intermediate via connected to a second terminal of said metal resistor, said second intermediate via being further connected to a second metal segment patterned in said second interconnect metal layer;

a dielectric cap layer situated between said metal resistor and said second intermetallic dielectric layer.

Claim 2 (original): The integrated circuit chip of claim 1 wherein said metal resistor is selected from the group consisting of titanium nitride and tantalum nitride.

Claim 3 (original): The integrated circuit chip of claim 1 wherein said first interconnect metal layer comprises aluminum.

Claim 4 (original): The integrated circuit chip of claim 1 wherein said first intermetallic dielectric layer comprises HDPCVD silicon dioxide.

Claim 5 (original): The integrated circuit chip of claim 1 wherein said second intermetallic dielectric layer comprises undoped silica glass.

Claim 6 (canceled).

Claim 7 (currently amended): The integrated circuit chip of claim 6 1 wherein said dielectric cap layer comprises silicon nitride.

Claim 8 (original): The integrated circuit chip of claim 1 further comprising an oxide cap layer situated between said metal resistor and said first intermetallic dielectric layer.

Claim 9 (original): The integrated circuit chip of claim 8 wherein said oxide cap layer comprises PECVD silicon dioxide.

Claim 10 (currently amended): An integrated circuit chip comprising:

- a first interconnect metal layer;
- a first intermetallic dielectric layer situated over said first interconnect metal layer;
- a metal resistor situated over said first intermetallic dielectric layer and below a second intermetallic dielectric layer;
- a second interconnect metal layer over said second intermetallic dielectric layer;
- a first intermediate via connected to a first terminal of said metal resistor;
- a second intermediate via connected to a second terminal of said metal resistor;
- a dielectric cap layer situated between said metal resistor and said second intermetallic dielectric layer.

Claim 11 (original): The integrated circuit chip of claim 10 wherein said metal resistor is selected from the group consisting of titanium nitride and tantalum nitride.

Claim 12 (original): The integrated circuit chip of claim 10 wherein said first intermetallic dielectric layer comprises HDPCVD silicon dioxide.

Claim 13 (original): The integrated circuit chip of claim 10 wherein said second intermetallic dielectric layer comprises undoped silica glass.

Claim 14 (canceled).

Claim 15 (currently amended): The integrated circuit chip of claim 14 10 wherein said dielectric cap layer comprises silicon nitride.

Claim 16 (original): The integrated circuit chip of claim 10 wherein said first interconnect metal layer comprises aluminum.

Claim 17 (original): The integrated circuit chip of claim 10 further comprising an oxide cap layer situated between said metal resistor and said first intermetallic dielectric layer.

Claim 18 (original): The integrated circuit chip of claim 17 wherein said oxide cap layer comprises PECVD silicon dioxide.

Claims 19-27 (canceled).